

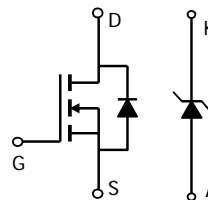
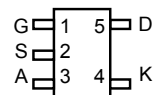
**AO3702**
**N-Channel Enhancement Mode Field Effect Transistor with Schottky Diode**
**General Description**

The AO3702/L uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge. A Schottky diode is provided to facilitate the implementation of a bidirectional blocking switch, or for DC-DC conversion applications. AO3702 and AO3702L are electrically identical.

- RoHs Complaint
- AO3702L is Halogen Free

**Features**

$V_{DS} (V) = 20V$   
 $I_D = 3.5A (V_{GS} = 4.5V)$   
 $R_{DS(ON)} < 62m\Omega (V_{GS} = 4.5V)$   
 $R_{DS(ON)} < 70m\Omega (V_{GS} = 2.5V)$   
 $R_{DS(ON)} < 85m\Omega (V_{GS} = 1.8V)$   
**SCHOTTKY**  
 $V_{DS} (V) = 20V, I_F = 1A, V_F < 0.5V @ 0.5A$

 SOT-23-5  
 Top View

**Absolute Maximum Ratings  $T_A=25^\circ C$  unless otherwise noted**

Parameter	Symbol	MOSFET	Schottky	Units
Drain-Source Voltage	$V_{DS}$	20		V
Gate-Source Voltage	$V_{GS}$	$\pm 8$		V
Continuous Drain Current <sup>A</sup>	$I_D$	$T_A=25^\circ C$	3.5	A
		$T_A=70^\circ C$	2.7	
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	25		
Schottky reverse voltage	$V_{KA}$		20	V
Continuous Forward Current <sup>A</sup>	$I_F$	$T_A=25^\circ C$	1	A
		$T_A=70^\circ C$	0.5	
Pulsed Forward Current <sup>B</sup>	$I_{FM}$		10	
Power Dissipation	$P_D$	$T_A=25^\circ C$	1.15	W
		$T_A=70^\circ C$	0.7	
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	-55 to 150	$^\circ C$

Parameter: Thermal Characteristics MOSFET		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$t \leq 10s$	$R_{\theta JA}$	80.3	110	$^\circ C/W$
	Steady-State		117	150	
Maximum Junction-to-Lead <sup>C</sup>	Steady-State	$R_{\theta JL}$	43	80	
Thermal Characteristics Schottky					
Maximum Junction-to-Ambient <sup>A</sup>	$t \leq 10s$	$R_{\theta JA}$	153	190	$^\circ C/W$
	Steady-State		173	220	
Maximum Junction-to-Lead <sup>C</sup>	Steady-State	$R_{\theta JL}$	103	140	

**Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V	20			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V T <sub>J</sub> =55°C			1 5	μA
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±8V			±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.5	0.68	1	V
I <sub>D(ON)</sub>	On state drain current	V <sub>GS</sub> =4.5V, V <sub>DS</sub> =5V	25			A
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =4.5V, I <sub>D</sub> =3.5A T <sub>J</sub> =125°C		50 70	62 90	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =3A		56	70	mΩ
		V <sub>GS</sub> =1.8V, I <sub>D</sub> =2.5A		66	85	
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =2A		15		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =1A, V <sub>GS</sub> =0V		0.7	1	V
I <sub>S</sub>	Maximum Body-Diode Continuous Current				1.6	A
<b>DYNAMIC PARAMETERS</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =10V, f=1MHz		260	320	pF
C <sub>oss</sub>	Output Capacitance			48		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			27		pF
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz		3	4.5	Ω
<b>SWITCHING PARAMETERS</b>						
Q <sub>g</sub>	Total Gate Charge	V <sub>GS</sub> =4.5V, V <sub>DS</sub> =10V, I <sub>D</sub> =3.5A		2.9	3.8	nC
Q <sub>gs</sub>	Gate Source Charge			0.4		nC
Q <sub>gd</sub>	Gate Drain Charge			0.6		nC
t <sub>D(on)</sub>	Turn-On Delay Time	V <sub>GS</sub> =4.5V, V <sub>DS</sub> =10V, R <sub>L</sub> =3Ω, R <sub>GEN</sub> =6Ω		2.5		ns
t <sub>r</sub>	Turn-On Rise Time			3.2		ns
t <sub>D(off)</sub>	Turn-Off Delay Time			21		ns
t <sub>f</sub>	Turn-Off Fall Time			3		ns
t <sub>rr</sub>	Body Diode Reverse Recovery Time		I <sub>F</sub> =3.5A, di/dt=100A/μs		14	19
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =3.5A, di/dt=100A/μs		3.4		nC
<b>SCHOTTKY PARAMETERS</b>						
V <sub>F</sub>	Forward Voltage Drop	I <sub>F</sub> =0.5A		0.37	0.5	V
I <sub>rm</sub>	Maximum reverse leakage current	V <sub>R</sub> =16V			0.1	mA
		V <sub>R</sub> =16V, T <sub>J</sub> =125°C			20	
C <sub>T</sub>	Junction Capacitance	V <sub>R</sub> =10V		52		pF
t <sub>rr</sub>	Schottky Reverse Recovery Time	I <sub>F</sub> =1A, di/dt=100A/μs		9.2	12	ns
Q <sub>rr</sub>	Schottky Reverse Recovery Charge	I <sub>F</sub> =1A, di/dt=100A/μs		1.7		nC

A: The value of R<sub>θJA</sub> is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t<sub>θJA</sub> ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R<sub>θJA</sub> is the sum of the thermal impedance from junction to lead R<sub>θJL</sub> and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

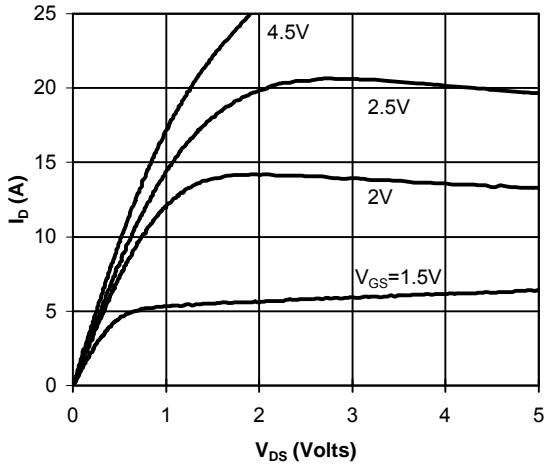


Fig 1: On-Region Characteristics

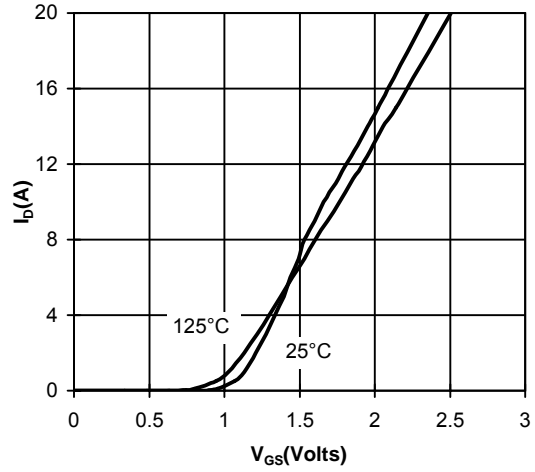


Figure 2: Transfer Characteristics

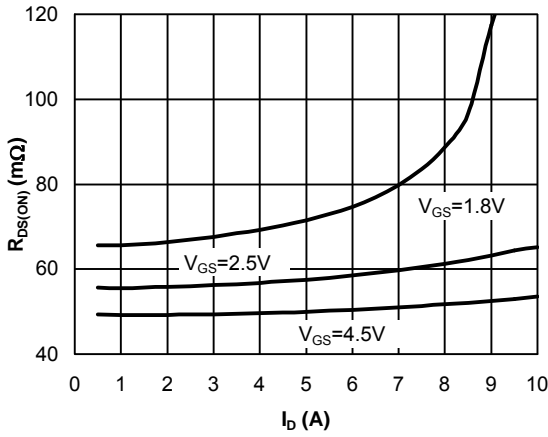


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

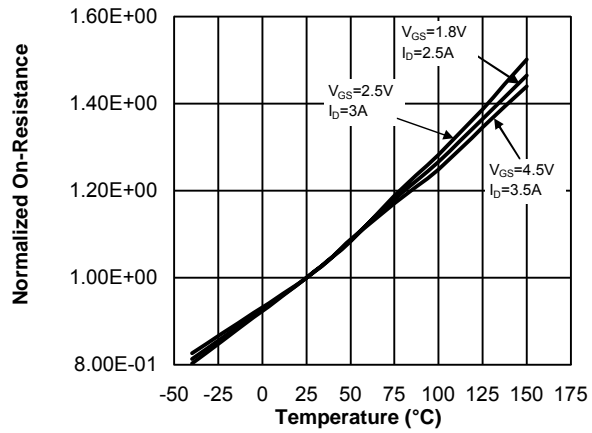


Figure 4: On-Resistance vs. Junction Temperature

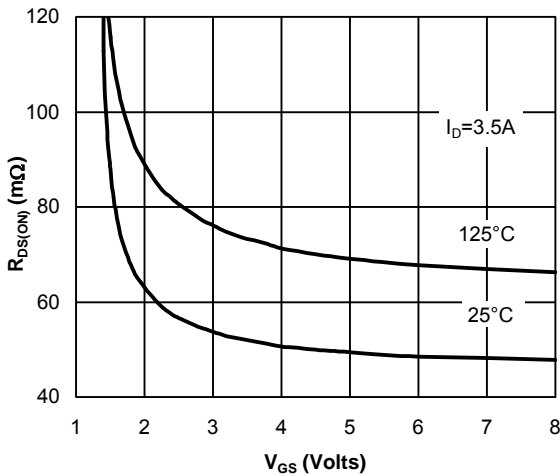


Figure 5: On-Resistance vs. Gate-Source Voltage

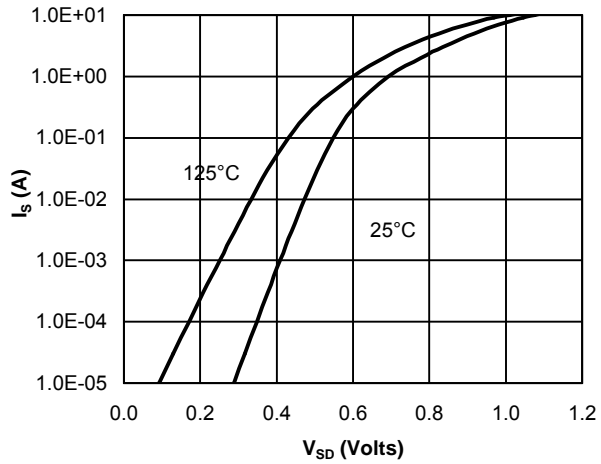


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

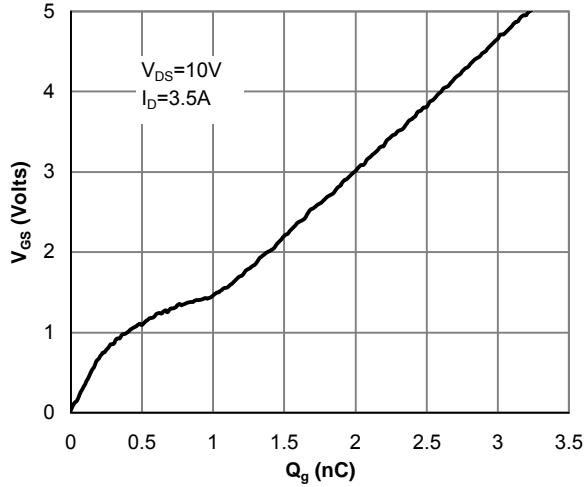


Figure 7: Gate-Charge Characteristics

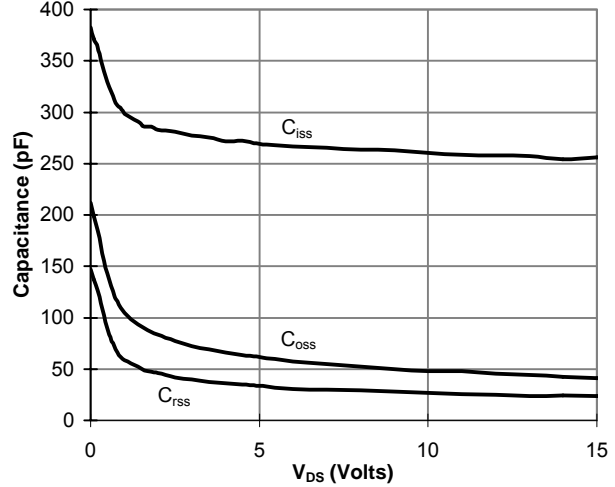


Figure 8: Capacitance Characteristics

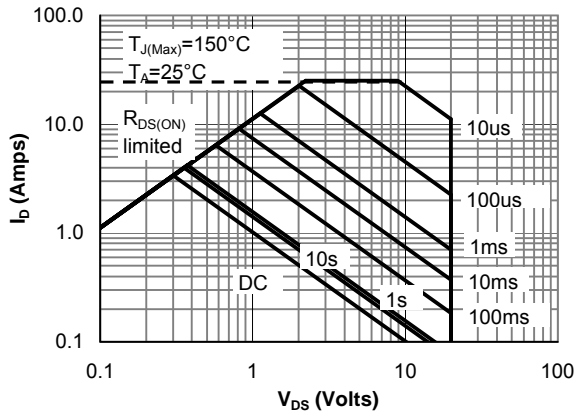


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

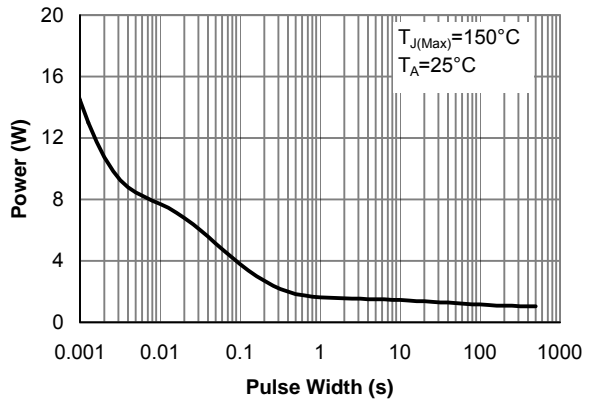


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

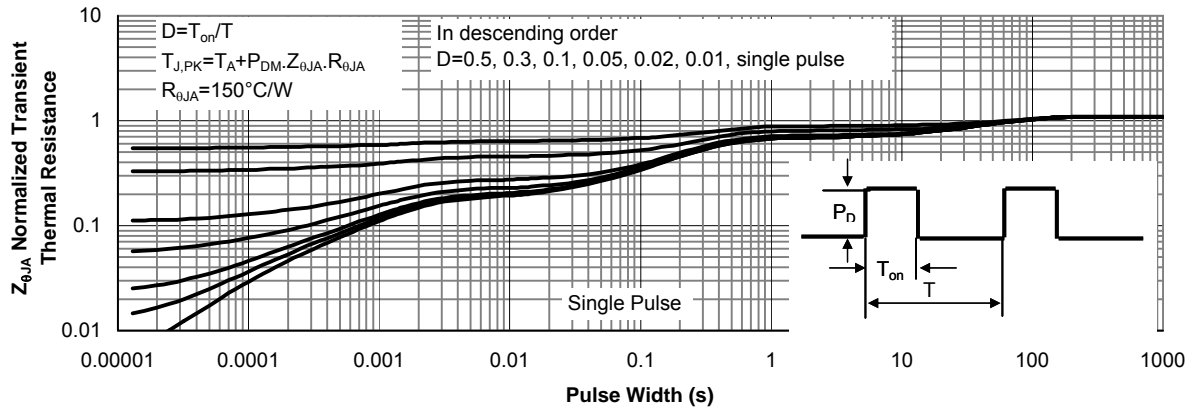


Figure 11: Normalized Maximum Transient Thermal Impedance

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS: SCHOTTKY

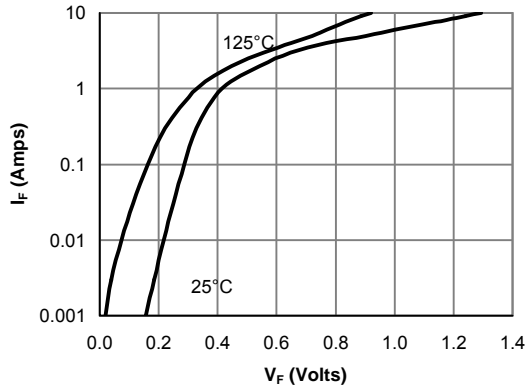


Figure 12: Schottky Forward Characteristics

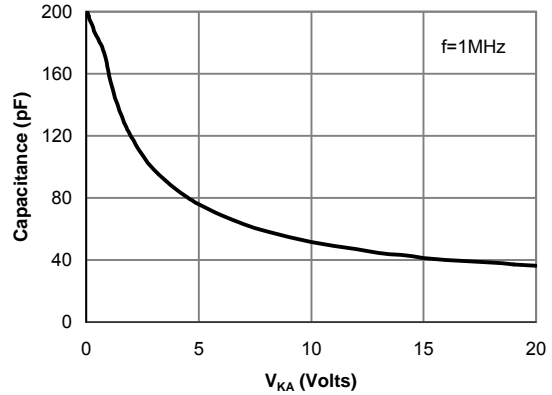


Figure 13: Schottky Capacitance Characteristics

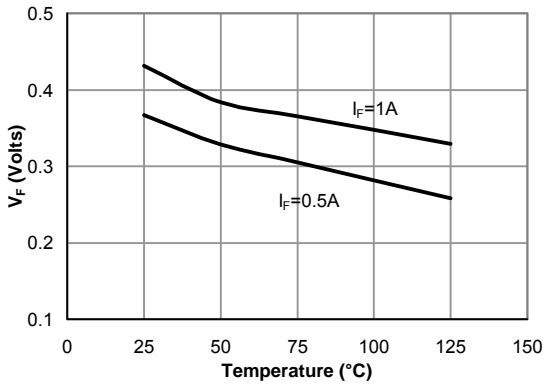


Figure 14: Schottky Forward Drop vs. Junction Temperature

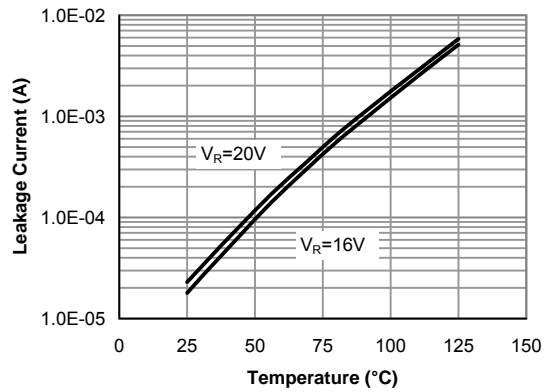


Figure 15: Schottky Leakage current vs. Junction Temperature

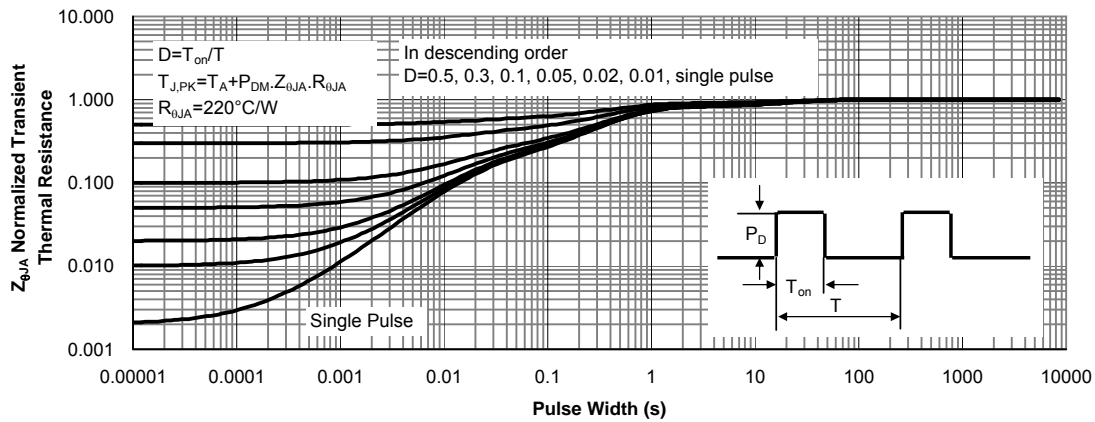


Figure 16: Schottky Normalized Maximum Transient Thermal Impedance